/ Descriptions

TO-263

Schottky Diode in a TO-263 Plastic Package.

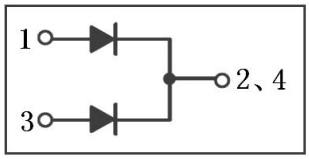
/ Features

Low power loss, high efficiency.

/ Applications

For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.

/ Equivalent Circuit



/ Pinning



PIN1 Anode PIN 2 4 Cathode PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Reverse Voltage	V_{RRM} V_{RWM} V_{RM}	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average forward rectified Current	I_F	2X5	A
Non Repetitive Peak Surge Current	I_{FSM}	125	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.5	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

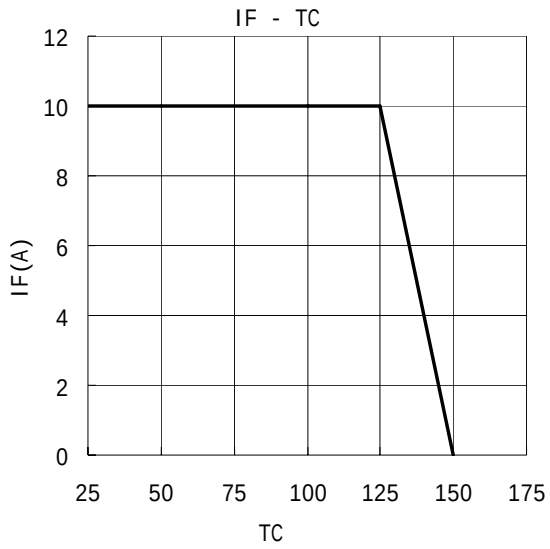
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	I_R =0.3mA	100			V
Forward Voltage	V_{FM}	I_F =5.0A T_j=25			0.85	V
		I_F =5.0A T_j=125			0.75	V
		I_F =10A T_j=25			0.95	V
		I_F =10A T_j=125			0.85	V
Instantaneous Reverse Current	I_R Note 1	V_R=100V T_j=25			10	uA
		V_R=70V T_j=125			1	mA
		V_R=100V T_j=125			5	mA

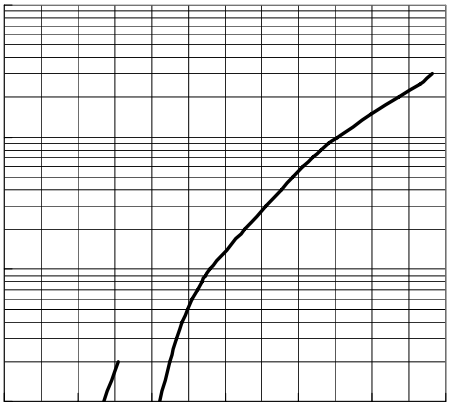
/Notes

1. /Short duration pulse test used to minimize self-heating effect.

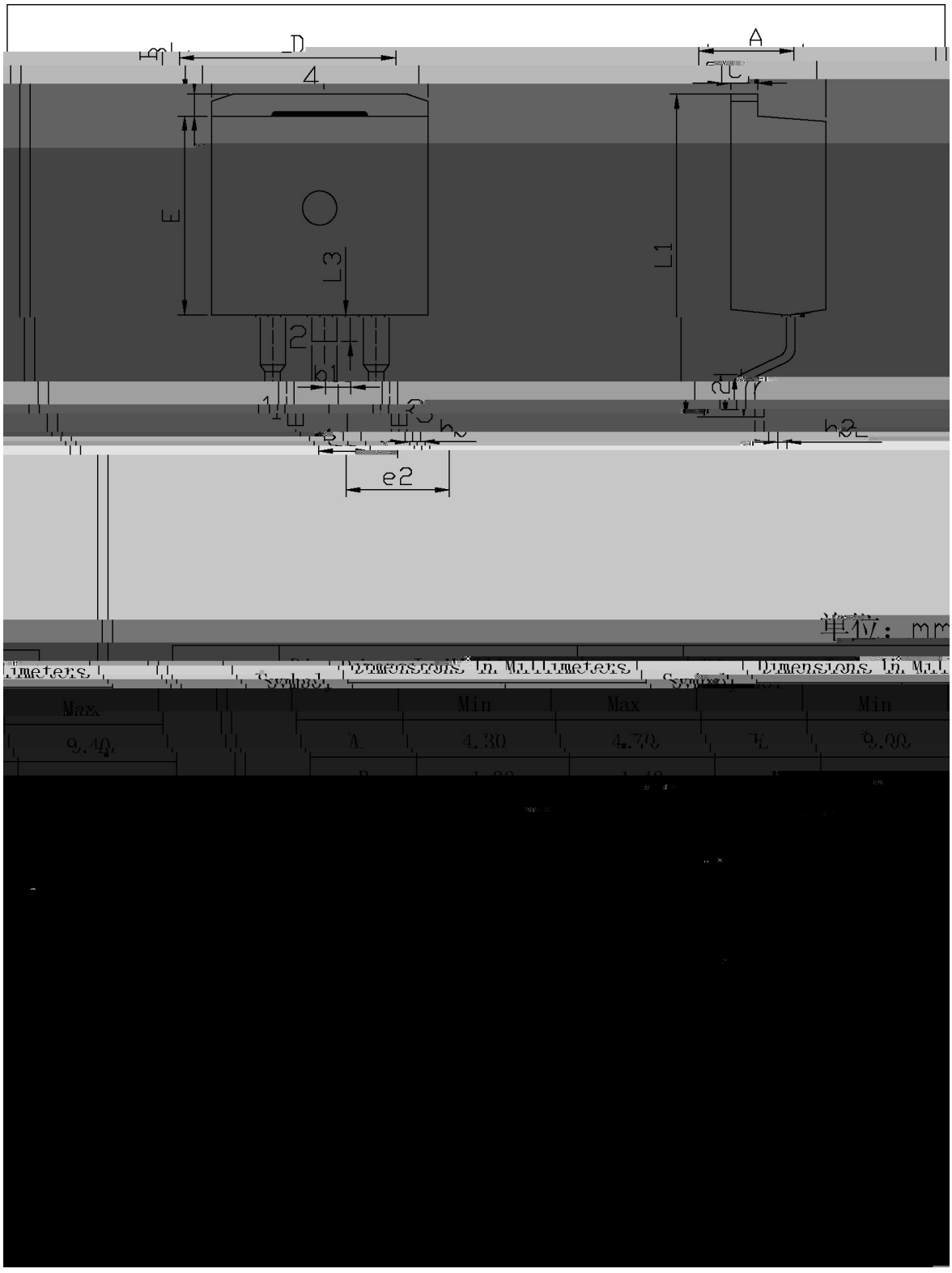
2. / Unless otherwise noted, values for the parameters of a single chip

/ Electrical Characteristic Curve

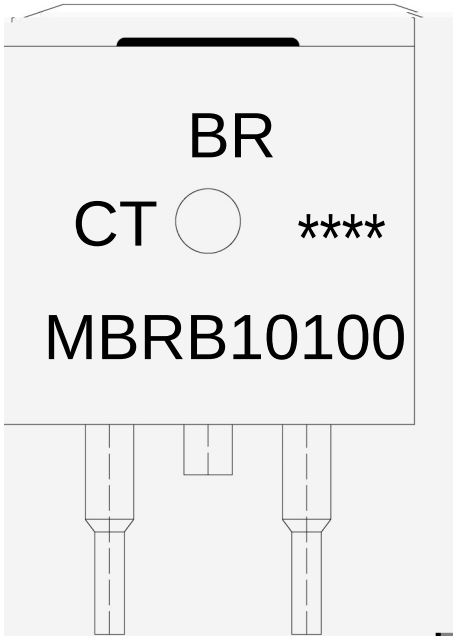




/ Package Dimensions



/ Marking Instructions



BR

MBRB10100

CT:

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Note:

BR:	Company Code
MBRB10100	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.